

1 5. (Amended) A thin film transistor including:

2 a back channel electrode,

3 wherein a voltage of a front channel positioned on the side of a gate wiring of said
B²⁴ 4 thin film transistor is made equal to a voltage of said back channel positioned on the side of a
5 back channel electrode by short-circuiting said back channel electrode to a gate electrode
6 through a contact-hole provided in a portion of a semiconductor layer forming said thin film
7 transistor, and

8 wherein a passivation film patterned to have a width equal to that of said back channel
9 electrode and said semiconductor layer are provided between said back channel and a gate
10 insulating film.

1 15. (Amended) A thin film transistor including:

2 a back channel electrode,

3 wherein a voltage of a front channel positioned on the side of a gate wiring of said
4 thin film transistor is made equal to a voltage of said back channel positioned on the side of a
B³ 5 back channel electrode by short-circuiting said back channel electrode to a gate electrode
6 through a contact-hole provided in a portion of a semiconductor layer forming said thin film
7 transistor, and

8 wherein said layer patterned to have a width equal to that of source and drain
9 electrodes of said thin film transistor is provided between said source and drain electrodes
10 and a gate insulating film of said film transistor.

1 16. (Amended) A thin film transistor including:

2 a back channel electrode,

3 wherein a voltage of a front channel positioned on the side of a gate wiring of said
4 thin film transistor is made equal to a voltage of said back channel positioned on the side of a
5 back channel electrode by short-circuiting said back channel electrode to a gate electrode
6 through a contact-hole provided in a portion of a semiconductor layer forming said thin film
7 transistor, and

8 wherein said layer has an ohmic contact layer on the side thereof, which is in contact
9 with source and drain electrodes of said film transistor.